1200V SiC N-Channel MOSFET

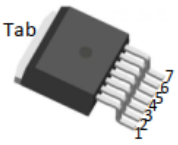
DESCRIPTION：

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(ON)}$
- Easy to Parallel
- Simple to Drive
- RoHS compliant.

V_{DS}	1200V
I_D (T_C=25℃)	46A
$R_{DS(ON)\_Typ.}$@V_{GS}=18V	59mΩ

TYPICAL APPLICATIONS：

- Power Factor Correction Modules
- Switch Mode Power Supplies
- DC-AC Inverters
- High Voltage DC-DC Converters



TO-263-7L

MAXIMUM RATINGS (at T_J = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	1200	V
Continuous Drain Current	Tc=25℃ Tc=100℃	I_D	46 35	A
Peak Drain Current	Pulse width tp limited by Tjmax	I_{DM}	105	A
Gate-Source Voltage		V_{GSmax}	-8/+22	V
Recommend Gate-Source Voltage		V_{GSop}	-4/+18	V
Power Dissipation	Tc=25℃ Tc=100℃	P_{TOT}	263 131	W
Operation Junction temperature		Tj	-40~+175	℃
Storage temperature		T_{STG}	-40~+175	℃

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Typical	Unit
Thermal resistance, junction - case		$R_{th(j-C)}$	0.57	℃/W

ELECTRICAL CHARATERISTICS (at T_J = 25 °C, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage VGS = 0V, ID = 100μA	$V_{(BR)DSS}$	1200			V
Zero Gate Voltage Drain Current VDS = 1200 V, VGS = 0 V	I_{DSS}		1		uA
Gate-Source Leakage Current VGS = 18V, VDS = 0V	I_{GSS}			250	nA
Gate-Source Threshold Voltage VDS = VGS, ID = 5mA Tj=25℃ VDS = VGS, ID = 5mA Tj=150℃ VDS = VGS, ID = 5mA Tj=175℃	$V_{GS(th)}$	2.0	2.8 2.2 2.1	4.0	V
Drain-Source On-State Resistance VGS = 18V, ID = 20A Tj=25℃ VGS = 18V, ID = 20A Tj=150℃ VGS = 18V, ID = 20A Tj=175℃	$R_{DS(on)}$		59 81 90		mΩ
Internal Gate Resistance f=1MHz	$R_{G(INT)}$		0.98		Ω
Input capacitance f=1MHz, VDS=1000 V, VGS=0 V	C_{iss}		2451		pF
Output capacitance f=1MHz, VDS=1000 V, VGS=0 V	C_{oss}		79		pF
Reverse transfer capacitance f=1MHz, VDS=1000 V, VGS=0 V	C_{rss}		6		pF
Total Gate Charge VDS= 800V, ID= 20A,VGS= -4/18V	Q_G		103		nC
Gate to Source Charge VDS= 800V, ID= 20A,VGS= -4/18V	Q_{GS}		29		nC
Gate to Drain Charge VDS= 800V, ID= 20A,VGS= -4/18V	Q_{GD}		36		nC
Turn-on Delay Time VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	$td_{(ON)}$		14		ns
Rise Time VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	tr		10		ns
Turn-off Delay Time VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	$td_{(OFF)}$		22		ns
Fall Time VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	tf		9		ns

Turn-on Switching Energy VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	$E_{(ON)}$		125		uJ
Turn-off Switching Energy VDD=800 V, ID=20A, VGS= -4/18V, RG=0Ω	$E_{(OFF)}$		25		uJ

Body Diode

ELECTRICAL CHARATERISTICS (at T_J = 25 °C, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Diode Forward Voltage VGS = -4V, ISD = 20A Tj=25℃ VGS = -4V, ISD = 20A Tj=175℃	V_{SD}		4.6 4.2		V
Continuous Diode Forward Current VGS = -4V, Tc=25℃ VGS = -4V, Tc=100℃	I_S		43 23		A
Revers Recovery Time VR=800 V, ISD=20A, VGS= -4V, di/dt = 3830A/us	Trr		56		ns
Revers Recovery Charge VR=800 V, ISD=20A, VGS= -4V, di/dt = 3830A/us	Qrr		76		nC
Peak Revers Recovery Current VR=800 V, ISD=20A, VGS= -4V, di/dt = 3830A/us	I_{rrm}		13		A

Typical Characteristics

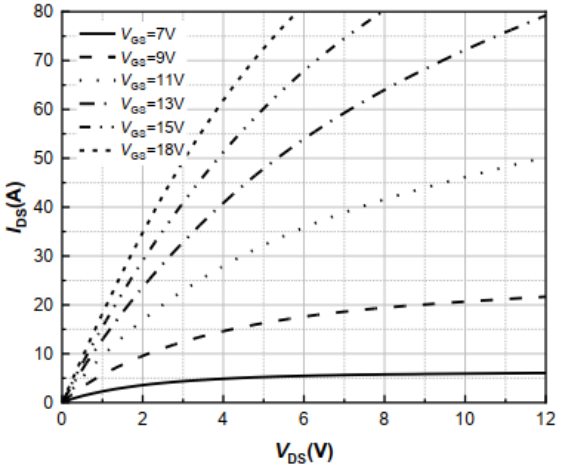


Figure 1. Typical output characteristics (Tj=25℃)

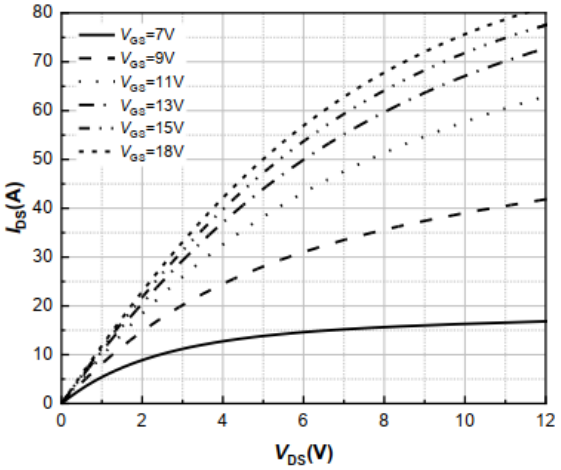


Figure 2. Typical output characteristics (Tj=175℃)

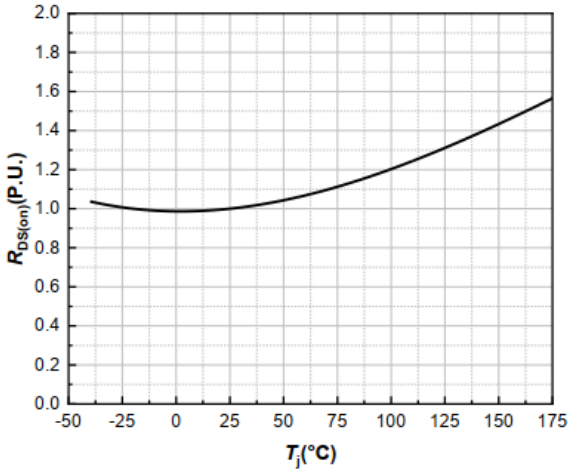


Figure 3. Normalized Resistance v/s Temperature

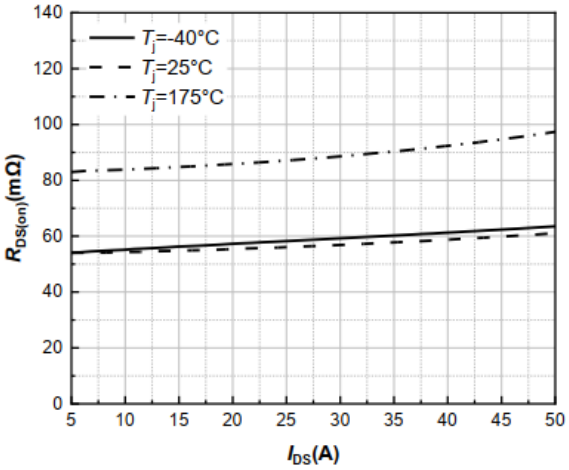


Figure 4. On-Resistance vs. Drain Current For Various Temperatures

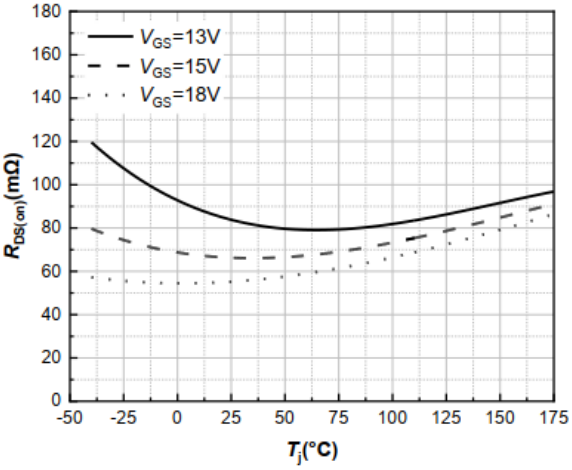


Figure 5. On-Resistance vs. Temperature For Various Gate Voltage

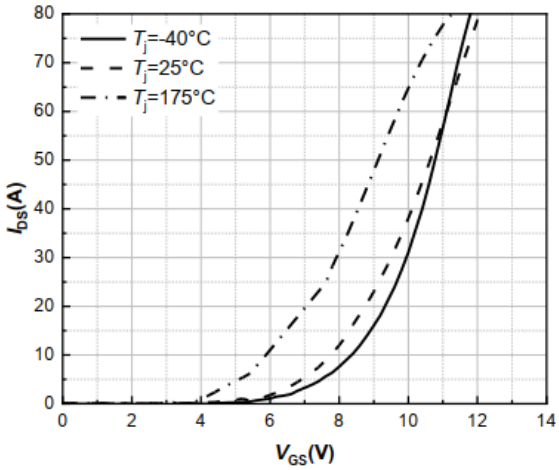


Figure 6. Transfer Characteristic for Various Junction Temperatures VDS=20V

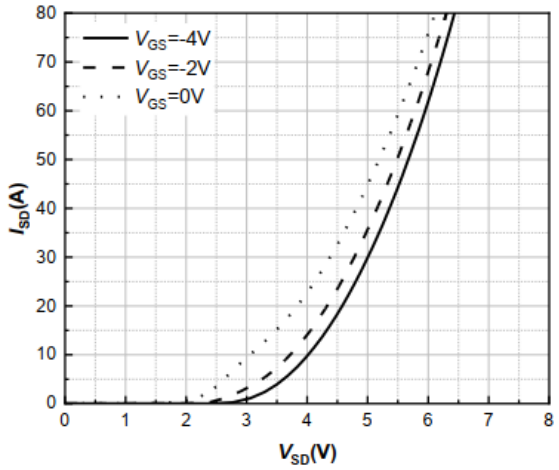


Figure 7. Body Diode Characteristic Tj=25°C

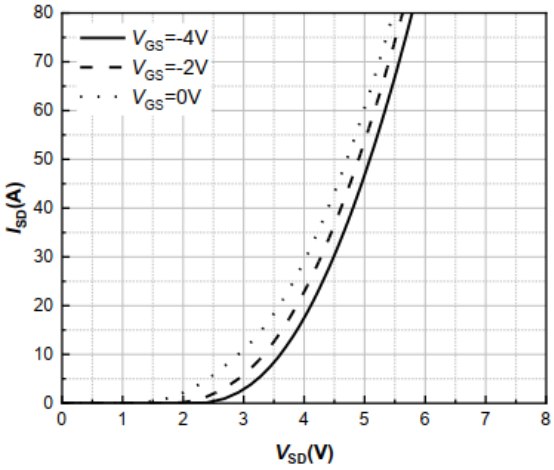


Figure 8. Body Diode Characteristic Tj=175°C

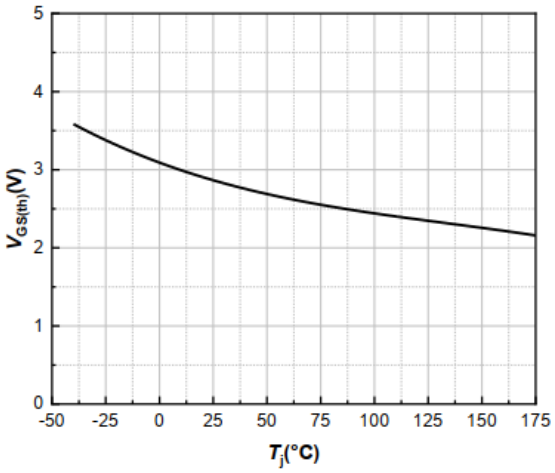


Figure 9. Threshold Voltage vs.Temperature

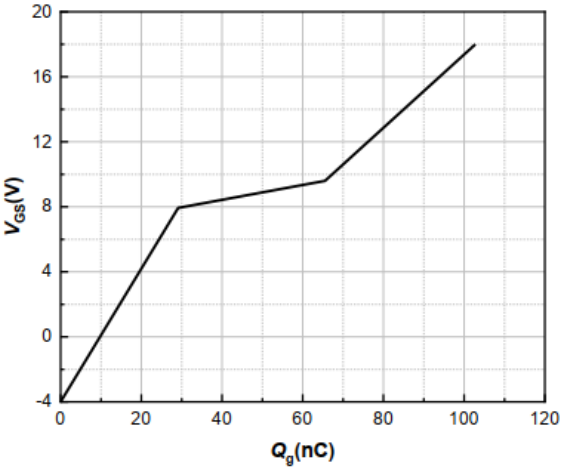


Figure 10. Gate Charge Characteristics

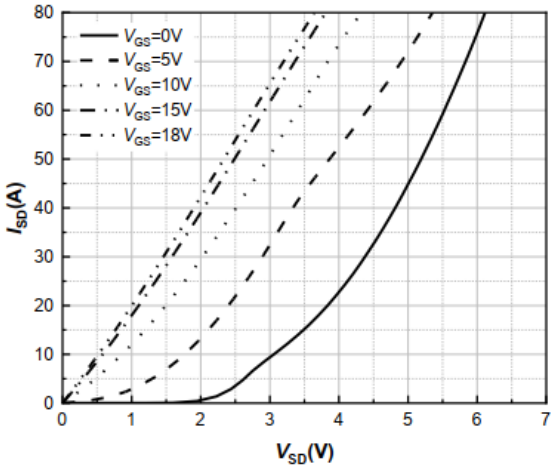


Figure 11. 3rd Quadrant Characteristic Tj=25°C

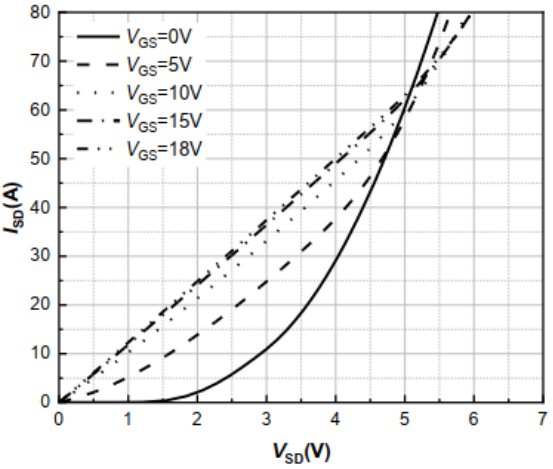


Figure 12. 3rd Quadrant Characteristic Tj=175°C

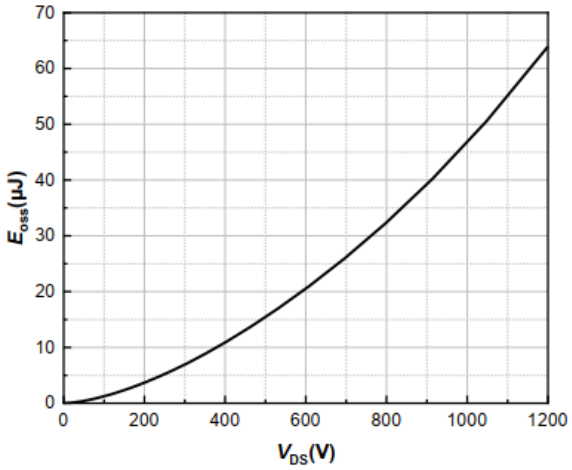


Figure 13. Output Capacitor Stored Energy

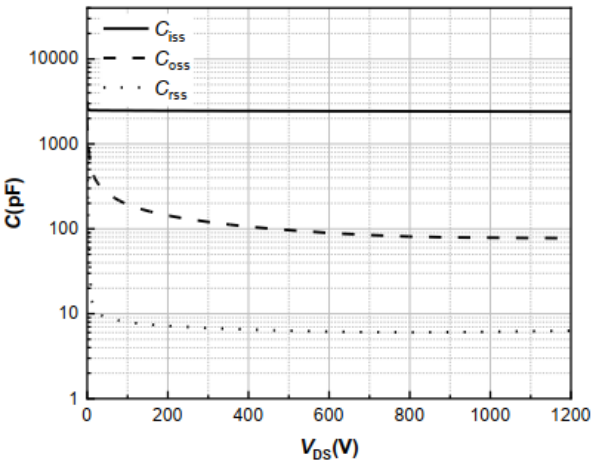


Figure 14. Capacitances vs. Drain-Source

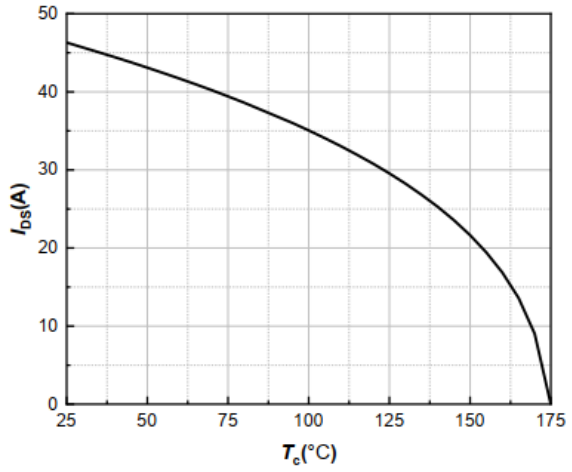


Figure 15. Continuous Drain Current Derating vs. Case Temperature

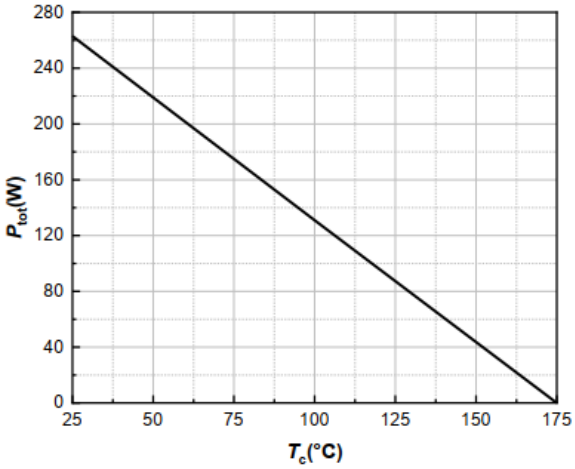


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

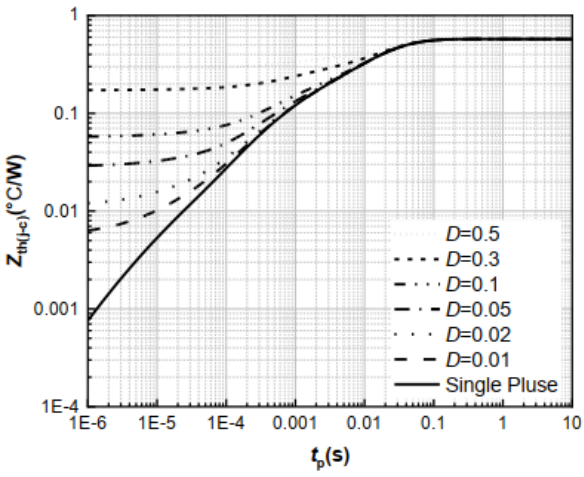


Figure 17. Transient Thermal Impedance

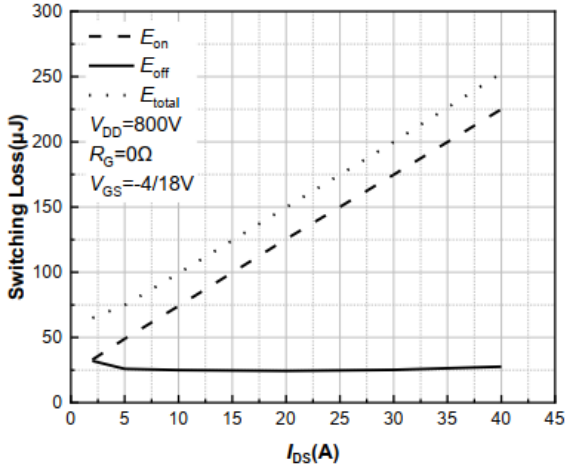


Figure 18. Clamped Inductive Switching Energy vs. Drain Current

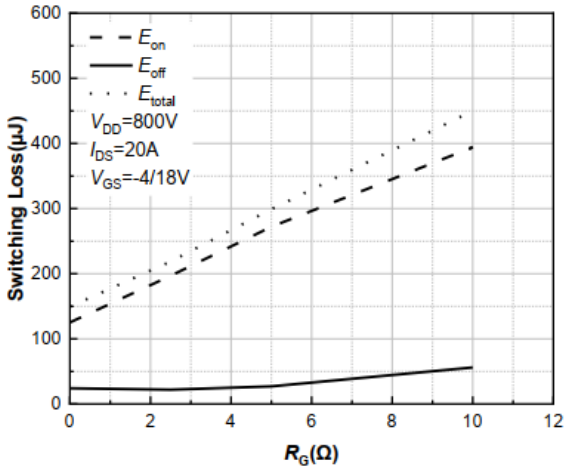


Figure 19. Clamped Inductive Switching Energy vs. RG

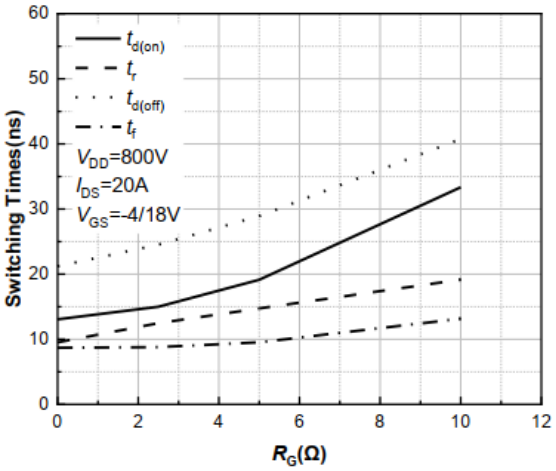


Figure 20. Switching Times vs. RG

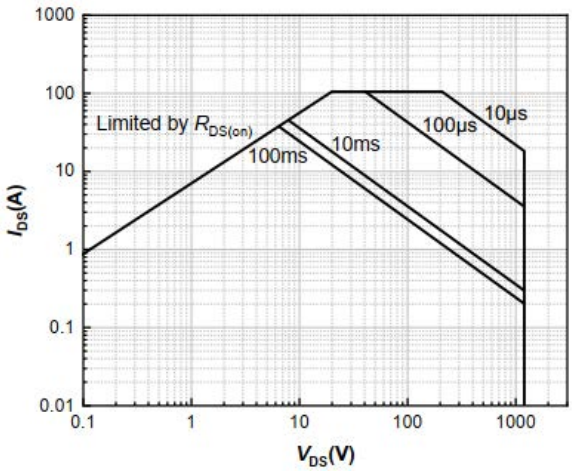
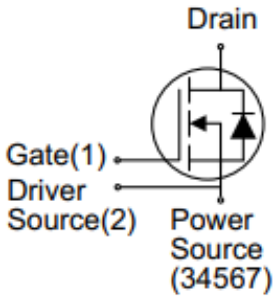
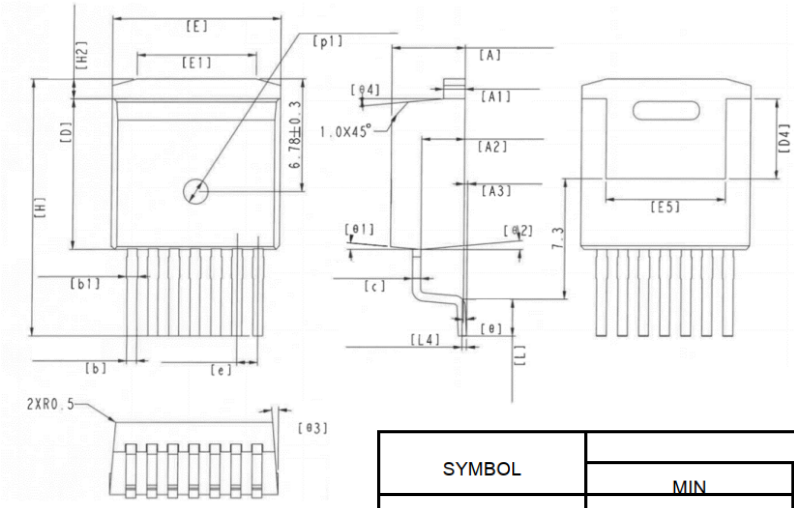


Figure 21. Safe Operating Area

• Circuit diagram



• TO-263-7L Package outlines : Dimensions in (mm)



SYMBOL	Unit: mm		
	MIN	NOM	MAX
A	4.30	4.43	4.56
A1	1.2	1.3	1.4
A2	2.45	2.60	2.75
A3	0.00	0.13	0.25
b	0.5	0.6	0.7
b1	0.6	0.7	0.9
c	0.45	0.50	0.60
D	8.93	9.08	9.23
D4	4.65	4.80	4.95
E	10.08	10.18	10.28
E1	6.5	7.0	7.5
E5	6.82	7.22	7.62
e	1.27BSC		
H	15.0	15.5	16.0
H2	0.98	1.20	1.42
L	1.9	2.2	2.5
L4	0.25BSC		
p1	1.4	1.5	1.6
θ	0°	3°	7°
θ1	3°	5°	7°
θ2	3°	5°	7°
θ3	3°	5°	7°
θ4	3°	5°	7°

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